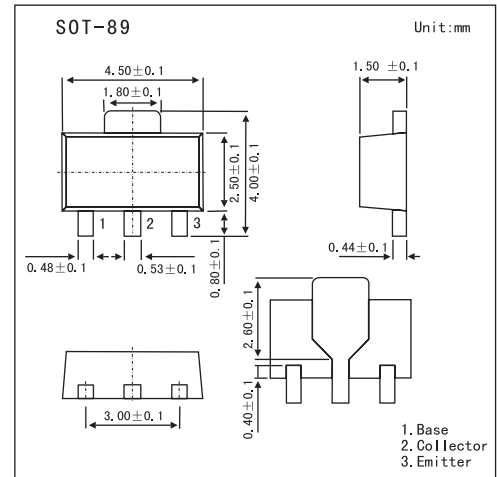


## Power Transistor

## 2SB1427

## ■ Features

- Low saturation voltage,  
typically  $V_{CE(sat)} = -0.5V$  at  $I_C/I_B = -1A/-50mA$ .
- Excellent DC current gain characteristics.

■ Absolute Maximum Ratings  $T_a = 25^\circ C$ 

Parameter	Symbol	Rating	Unit
Collector-base voltage	$V_{CBO}$	-20	V
Collector-emitter voltage	$V_{CEO}$	-20	V
Emitter-base voltage	$V_{EBO}$	-6	V
Collector current	$I_C$	-2	A
Collector current(Pulse)	$I_{CP}^*$	-3	A
Collector power dissipation	$P_C$	0.5	W
Junction temperature	$T_j$	150	$^\circ C$
Storage temperature	$T_{stg}$	-55 to +150	$^\circ C$

\* Single pulse,  $P_w=10ms$

■ Electrical Characteristics  $T_a = 25^\circ C$ 

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$BV_{CBO}$	$I_C = -50\mu A$	-20			V
Collector-emitter breakdown voltage	$BV_{CEO}$	$I_C = -1mA$	-20			V
Emitter-base breakdown voltage	$BV_{EBO}$	$I_E = -50\mu A$	-6			V
Collector cutoff current	$I_{CBO}$	$V_{CB} = -16V$			-0.5	$\mu A$
Emitter cutoff current	$I_{EBO}$	$V_{EB} = -5V$			-0.5	$\mu A$
DC current transfer ratio	$V_{CE(sat)}$	$I_C = -1A, I_B = -500mA$			-0.5	V
Collector-emitter saturation voltage	$h_{FE}$	$V_{CE} = -6V, I_C = -0.5A$	390		820	
Transition frequency	$C_{ob}$	$V_{CE} = -10V, I_E = 10mA, f = 30MHz$		90		MHz
Output capacitance	$f_T$	$V_{CB} = -10V, I_E = 0A, f = 1MHz$		30		pF

## ■ Marking

Marking	BJE
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